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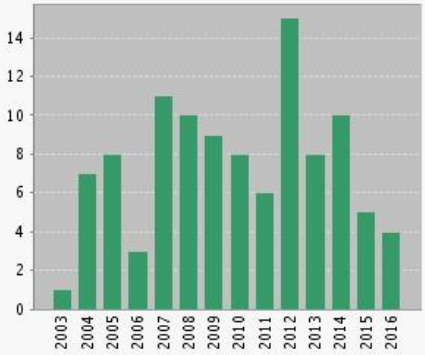

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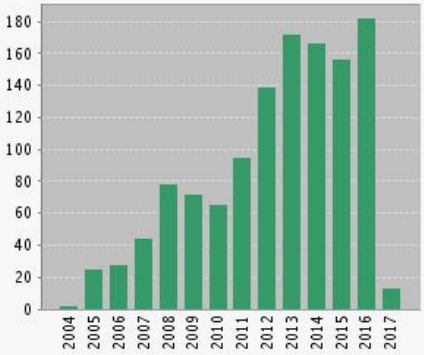

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	2013	2014	2015	2016	2017	Total	Average Citations per Year
	172	167	157	182	13	1242	88.71
1. **Low-power switching of nonvolatile resistive memory using hafnium oxide** By: Lee, Heng-Yuan; Chen, Pang-Shiu; Wang, Ching-Chiun; et al. Conference: International Conference on Solid State Devices and Materials Location: Pacifico Yokohama, Yokohama, JAPAN Date: SEP 13-15, 2006 Sponsor(s): Japan Soc Appl Phys & Technol; IEEE Electron Devices Soc JAPANESE JOURNAL OF APPLIED PHYSICS PART 1-REGULAR PAPERS BRIEF COMMUNICATIONS & REVIEW PAPERS Volume: 46 Issue: 4B Pages: 2175-2179 Published: APR 2007	19	14	8	4	0	102	9.27
2. **Charge trapping characteristics of atomic-layer-deposited HfO2 films with Al2O3 as a blocking oxide for high-density non-volatile memory device applications** By: Maikap, S.; Lee, H. Y.; Wang, T-Y; et al. SEMICONDUCTOR SCIENCE AND TECHNOLOGY Volume: 22 Issue: 8 Pages: 884-889 Published: AUG 2007	11	9	7	15	1	77	7.00
3. **Mobility-enhancement technologies** By: Liu, CW; Maikap, S; Yu, CY IEEE CIRCUITS & DEVICES Volume: 21 Issue: 3 Pages: 21-36 Published: MAY-JUN 2005	5	8	2	4	0	66	5.08
4. **Nanocrystals for silicon-based light-emitting and memory devices** By: Ray, S. K.; Maikap, S.; Banerjee, W.; et al. JOURNAL OF PHYSICS D-APPLIED PHYSICS Volume: 46 Issue: 15 Article Number: 153001 Published: APR 17 2013	9	13	14	16	0	52	10.40
5. **TaO (x) -based resistive switching memories: prospective and challenges** By: Prakash, Amit; Jana, Debanjan; Maikap, Siddheswar	1	16	19	13	1	50	10.00

NANOSCALE RESEARCH LETTERS Volume: 8 Article Number: 418 Published: OCT 9 2013							
6. **Ge outdiffusion effect on flicker noise in strained-Si nMOSFETs** By: Hua, WC; Lee, MH; Chen, PS; et al. IEEE ELECTRON DEVICE LETTERS Volume: 25 Issue: 10 Pages: 693-695 Published: OCT 2004	1	1	2	3	0	48	3.43
7. **Charge storage characteristics of atomic layer deposited RuOx nanocrystals** By: Maikap, S.; Wang, T. Y.; Tzeng, P. J.; et al. APPLIED PHYSICS LETTERS Volume: 90 Issue: 25 Article Number: 253108 Published: JUN 18 2007	4	1	1	1	0	40	3.64
8. **Band offsets and charge storage characteristics of atomic layer deposited high-k HfO2/TiO2 multilayers** By: Maikap, S.; Wang, T.-Y.; Tzeng, P.-J.; et al. APPLIED PHYSICS LETTERS Volume: 90 Issue: 26 Article Number: 262901 Published: JUN 25 2007	5	4	2	1	1	34	3.09
9. **Bipolar Resistive Switching Memory Using Cu Metallic Filament in Ge0.4Se0.6 Solid Electrolyte** By: Rahaman, S. Z.; Maikap, S.; Chiu, H. -C.; et al. ELECTROCHEMICAL AND SOLID STATE LETTERS Volume: 13 Issue: 5 Pages: H159-H162 Published: 2010	2	2	8	2	0	32	4.00
10. **Excellent resistive memory characteristics and switching mechanism using a Ti nanolayer at the Cu/TaOx interface** By: Rahaman, Sheikh Ziaur; Maikap, Siddheswar; Tien, Ta-Chang; et al. NANOSCALE RESEARCH LETTERS Volume: 7 Article Number: 345 Published: JUN 26 2012	6	7	11	5	1	31	5.17

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